

	Hits	Search Text	DBs
14	45	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6) near16 (size or small\$3 or area))) and ((photoresist or resist) same (opening or via or hole) same (fill\$4 or remain\$4) same (photomask or mask or reticle) same ((light\$4 near9 shield\$4) or (light near9 block\$4) or (transparent)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
15	3	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6) near16 (size or small\$3 or area))) and ((photoresist or resist) same (opening or via or hole) same (fill\$4 or remain\$4)) and ((substrate or wafer or object) same (ILD or inter\$6layer or dielectric) same (((etch near4 stop) or etch\$4resist\$4) near9 (layer or coat\$4 or film)) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	3	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6) near16 (size or small\$3 or area))) and ((photoresist or resist) same (opening or via or hole) same (fill\$4 or remain\$4 or bur\$5) same (photomask or mask or reticle)) and ((substrate or wafer or object) same (ILD or inter\$6layer or dielectric) same ((etch near4 stop) or etch\$4resist\$4) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
18	3	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6) near16 (size or small\$3 or area))) and ((photoresist or resist) same (opening or via or hole) same (fill\$4 or remain\$4 or bur\$5) same (photomask or mask or reticle)) and ((substrate or wafer or object) same (ILD or inter\$6layer or dielectric) same (((etch near4 stop) or etch\$4resist\$4) near9 (layer or coat\$4 or film)) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
19	3	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6) near16 (size or small\$3 or area))) and ((photoresist or resist) same (opening or via or hole) same (fill\$4 or remain\$4 or bur\$5)) and ((substrate or wafer or object) same (ILD or inter\$6layer or dielectric) same ((etch near4 stop) or etch\$4resist\$4) same (resist or photoresist)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
20	40	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6) near16 (size or small\$3 or area))) and ((photoresist or resist) same (opening or via or hole) same (fill\$4 or remain\$4 or bur\$5)) and ((ILD or inter\$6layer or dielectric) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
22	237	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3) same (fill\$4 or remain\$4 or bur\$5)) and ((ILD or inter\$6layer or dielectric) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
23	219	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near "22" (via or hole or trench\$3) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3) same (fill\$4 or remain\$4 or bur\$5)) and ((ILD or inter\$6layer or dielectric) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB